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PRODUCT RELIABILITY REPORT
FOR

DS3502, Rev A1

Maxim Integrated Products

4401 South Beltwood Parkway
Dallas, TX 75244-3292

Prepared by:

Don Lipps
Staff Reliability Engineer
MAXIM Integrated Products
4401 South Beltwood Pkwy.
Dallas, TX 75244-3292
Email: don.lipps@dalsemi.com
ph: 972-371-3739
fax: 972-371-6016

Conclusion:

The following qualification successfully meets the quality and reliability standards required of all Dallas Semiconductor products:

DS3502, Rev A1

In addition, Dallas Semiconductor's continuous reliability monitor program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards. The current status of the reliability monitor program can be viewed at http://www.maxim-ic.com/TechSupport /dsreliability.html.

Device Description:

A description of this device can be found in the product data sheet. You can find the product data sheet at http://dbserv.maxim-ic.com/l_datasheet3.cfm.

Reliability Derating:

The Arrhenius model will be used to determine the acceleration factor for failure mechanisms that are temperature accelerated.

AfT = exp((Ea/k)*(1/Tu - 1/Ts)) = tu/ts
AfT = Acceleration factor due to Temperature
tu = Time at use temperature (e.g. 55°C)
ts = Time at stress temperature (e.g. 125°C)
k = Boltzmann's Constant (8.617 x 10-5 eV/°K)
Tu = Temperature at Use (°K)
Ts = Temperature at Stress (°K)
Ea = Activation Energy (e.g. 0.7 ev)

The activation energy of the failure mechanism is derived from either internal studies or industry accepted standards, or activation energy of 0.7ev will be used whenever actual failure mechanisms or their activation energies are unknown. All deratings will be done from the stress ambient temperature to the use ambient temperature.

An exponential model will be used to determine the acceleration factor for failure mechanisms, which are voltage accelerated.

AfV = exp(B*(Vs - Vu))
AfV = Acceleration factor due to Voltage
Vs = Stress Voltage (e.g. 7.0 volts)
Vu = Maximum Operating Voltage (e.g. 5.5 volts)
B = Constant related to failure mechanism type (e.g. 1.0, 2.4, 2.7, etc.)

The Constant, B, related to the failure mechanism is derived from either internal studies or industry accepted standards, or a B of 1.0 will be used whenever actual failure mechanisms or their B are unknown. All deratings will be done from the stress voltage to the maximum operating voltage. Failure rate data from the operating life test is reported using a Chi-Squared statistical model at the 60% or 90% confidence level (Cf).

The failure rate, Fr, is related to the acceleration during life test by:

Fr = X/(ts * AfV * AfT * N * 2)
X = Chi-Sq statistical upper limit
N = Life test sample size

Failure Rates are reported in FITs (Failures in Time) or MTTF (Mean Time To Failure). The FIT rate is related to MTTF by:

MTTF = 1/Fr

NOTE: MTTF is frequently used interchangeably with MTBF.

The calculated failure rate for this device/process is:

FAILURE RATE:	**MTTF (YRS):**	**21360**	**FITS:**	**5.3**
	DEVICE HOURS:	**181784**	**FAILS:**	**0**

Only data from Operating Life or similar stresses are used for this calculation.

The parameters used to calculate this failure rate are as follows:

Cf: 60% **Ea: 0.7** **B: 0** **Tu: 25 °C** **Vu: 5.5 Volts**

The reliability data follows. At the start of this data is the device information. The next section is the detailed reliability data for each stress. The reliability data section includes the latest data available and may contain some generic data. "*" after DATE CODE denotes specific product data.

Device Information:

Process:	E6WA-2P2M,HPVt,E2,EPROGVt,TCZ,PF ALOCOS:GOI
Passivation:	Passivation w/Nov TEOS Oxide-Nitride
Die Size:	57 x 60
Number of Transistors:	8021
Interconnect:	Aluminum / 0.5% Copper
Gate Oxide Thickness:	150 Å

ELECTRICAL CHARACTERIZATION

DESCRIPTION	DATE CODE		CONDITION	READPOINT		QTY	FAILS	FA#
ESD SENSITIVITY	0802	*	EOS/ESD S5.1 HBM 500 VOLTS	1	PUL'S	3	0	
ESD SENSITIVITY	0802	*	EOS/ESD S5.1 HBM 1000 VOLTS	1	PUL'S	3	0	
ESD SENSITIVITY	0802	*	EOS/ESD S5.1 HBM 2000 VOLTS	1	PUL'S	3	0	
ESD SENSITIVITY	0802	*	EOS/ESD S5.1 HBM 3000 VOLTS	1	PUL'S	3	1	No FA
ESD SENSITIVITY	0802	*	EOS/ESD S5.1 HBM 8000 VOLTS	1	PUL'S	3	2	No FA
LATCH-UP	0802	*	JESD78, I-TEST 125C			6	0	
LATCH-UP	0802	*	JESD78, V-SUPPLY TEST 125C			6	0	
ESD SENSITIVITY	0802	*	JESD22-C101 CDM 100 VOLTS	3	PUL'S	3	0	
ESD SENSITIVITY	0802	*	JESD22-C101 CDM 200 VOLTS	3	PUL'S	3	0	
ESD SENSITIVITY	0802	*	JESD22-C101 CDM 500 VOLTS	3	PUL'S	3	0	
ESD SENSITIVITY	0802	*	JESD22-C101 CDM 1000 VOLTS	3	PUL'S	3	0	
ESD SENSITIVITY	0802	*	JESD22-C101 CDM 2000 VOLTS	3	PUL'S	3	3	No FA
ESD SENSITIVITY	0802	*	JESD22-A115 MM 50 VOLTS	1	PUL'S	3	0	
ESD SENSITIVITY	0802	*	JESD22-A115 MM 100 VOLTS	1	PUL'S	3	0	
ESD SENSITIVITY	0802	*	JESD22-A115 MM 200 VOLTS	1	PUL'S	3	0	

ESD SENSITIVITY	0802	*	JESD22-A115 MM 400 VOLTS	1	PUL'S	3	3	No FA
					Total:		**9**	

OPERATING LIFE

DESCRIPTION	DATE CODE		CONDITION	READPOINT		QTY	FAILS	FA#
HIGH TEMP OP LIFE	0718		125C, 5.25 VOLTS	1000	HRS	45	0	
HIGH TEMP OP LIFE	0718		125C, 5.25 VOLTS	1000	HRS	45	0	
HIGH TEMP OP LIFE	0738		125C, 5.5 VOLTS	192	HRS	77	0	
HIGH TEMP OP LIFE	0802		125C, 5.5 V (PSA) & 15.0 V (PSB)	500	HRS	77	0	
HIGH TEMP OP LIFE	0802	*	125C, 5.5 V (PSA) & 15.0 V (PSB)	500	HRS	77	0	
					Total:		**0**	

W/E ENDURANCE AND DATA RET'N

DESCRIPTION	DATE CODE		CONDITION	READPOINT		QTY	FAILS	FA#
STORAGE LIFE	0718		150C	1000	HRS	77	0	
WRITE CYCLE STRESS (KCYS)	0738		25 C, 5.5 VOLTS	200	KCYS	77	0	
STORAGE LIFE			150C	96	HRS	77	0	
WRITE CYCLE STRESS (KCYS)	0750		70 C, 5.5V (PSA) & 15.0V (PSB)	10	KCYS	77	0	
WRITE CYCLE STRESS (KCYS)	0802	*	25 C, 5.5 V (PSA) & 15.0 V (PSB)	200	KCYS	77	0	
STORAGE LIFE		*	150C	96	HRS	72	0	
WRITE CYCLE STRESS (KCYS)	0802	*	85 C, 5.5 V (PSA) & 15.0 V (PSB)	50	KCYS	77	0	
STORAGE LIFE		*	150C	96	HRS	77	0	
WRITE CYCLE STRESS (KCYS)	0802		85 C, 5.5 V (PSA) & 15.0 V (PSB)	50	KCYS	77	0	
STORAGE LIFE			150C	96	HRS	74	0	
					Total:		**0**	

FAILURE RATE: **MTTF (YRS): 21360** **FITS: 5.3**

DEVICE HOURS: 181784 **FAILS: 0**